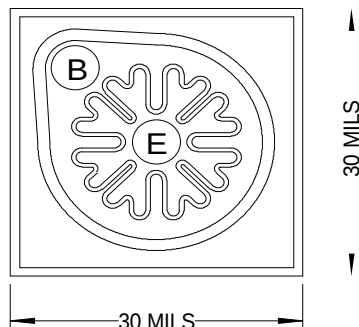


Chip Type 2C3762
Geometry 6706
Polarity PNP

Generic Packaged Parts:

**2N3467, 2N3467L, 2N3468,
2N3468L, 2N3762, 2N3762L,
2N3763, 2N3763L, 2N3764, 2N3765**



[Request Quotation](#)

Chip type **2C3762** by Semicoa Semiconductors provides performance similar to these devices.

Part Numbers:

[2N3467, 2N3467L, 2N3468, 2N3468L,
2N3762, 2N3762L, 2N3763, 2N3763L,
2N3764, 2N3765](#)

Product Summary:

APPLICATIONS: Designed for general purpose switching and amplifier applications.

Features: [Radiation graphs available](#)

Mechanical Specifications

Metallization	Top	Al - 20 kÅ min.
	Backside	Au - 6.5 kÅ nom.
Bonding Pad Size	Emitter	5.0 mils x 5.0 mils
	Base	5.0 mils x 5.0 mils
Die Thickness	8 mils nominal	
Chip Area	30 mils x 30 mils	
Top Surface	Silox Passivated	

Electrical Characteristics

$T_A = 25^\circ\text{C}$

Parameter	Test conditions	Min	Max	Unit
BV_{CBO}	$I_C = 100 \mu\text{A}, I_E = 0$	140	---	V dc
BV_{EBO}	$I_E = 100 \mu\text{A}, I_C = 0$	7.0	---	V dc
I_{CBO}	$V_{CB} = 40 \text{ V}, I_E = 0$	---	10	nA
h_{FE}	$I_C = 150 \text{ mA dc}, V_{CE} = 10 \text{ V}$	100	300	---

Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300 μs , duty cycle less than 2%.